

Absolute maximum ratings

(Ta=25°C)

Symbol	Specification	Unit
V _{CB0}	200	V
V _{CEO}	200	V
V _{EBO}	6	V
I _C	3	A
I _{CP}	6 (PW≤10ms, Du≤50%)	A
I _B	0.2	A
I _F	3 (PW≤0.5ms, Du≤25%)	A
I _{FSM}	6 (PW≤10ms, single)	A
V _R	200	V
P _T	5 (Ta=25°C)	W
	25 (Tc=25°C)	
T _j	150	°C
T _{stg}	-40 to +150	°C

Electrical characteristics

(Ta=25°C)

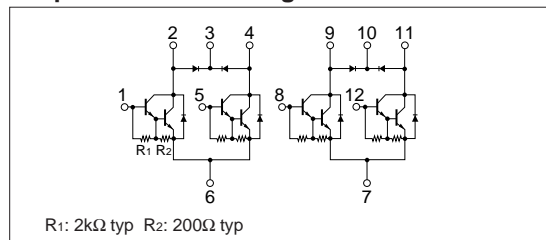
Symbol	Specification			Unit	Conditions
	min	typ	max		
I _{CBO}			10	μA	V _{CB} =200V
I _{EBO}			10	mA	V _{EB} =6V
V _{CEO}	200			V	I _C =10mA
h _{FE}	1000	6000	15000		V _{CE} =4V, I _C =1.5A
V _{CE(sat)}		1.1	1.5	V	I _C =1.5A, I _B =3mA
V _{BE(sat)}		1.7	2.0	V	
V _{FEC}			1.5	V	I _{FEC} =2.0A

Diode for flyback voltage absorption

(Ta=25°C)

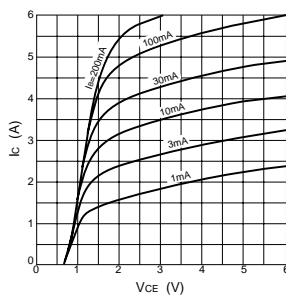
Symbol	Specification			Unit	Conditions
	min	typ	max		
V _R	200			V	I _R =10μA
V _F			1.6	V	I _F =1A
I _R			10	μA	V _R =200V
t _{rr}		100		ns	I _F =±100mA

Equivalent circuit diagram

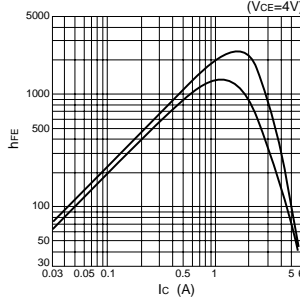


Characteristic curves

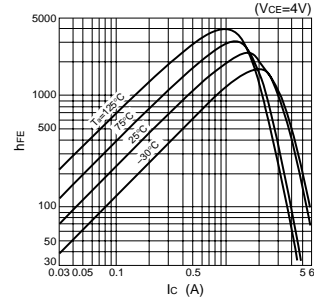
I_C-V_{CE} Characteristics (Typical)



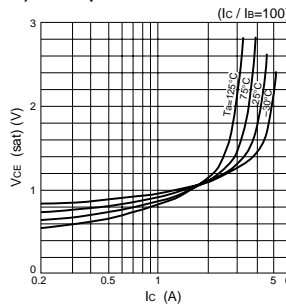
h_{FE}-I_C Characteristics (Typical)



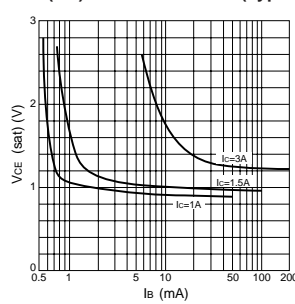
h_{FE}-I_C Temperature Characteristics (Typical)



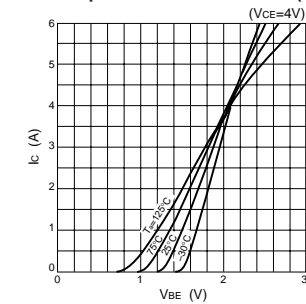
V_{CE(sat)}-I_C Temperature Characteristics (Typical)



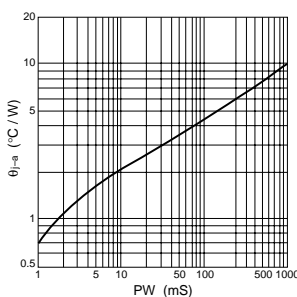
V_{CE(sat)}-I_B Characteristics (Typical)



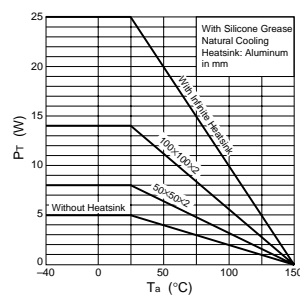
I_C-V_{BE} Temperature Characteristics (Typical)



θ_{JA}-PW Characteristics



P_T-T_a Characteristics



Safe Operating Area (SOA)

